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Data Sheet

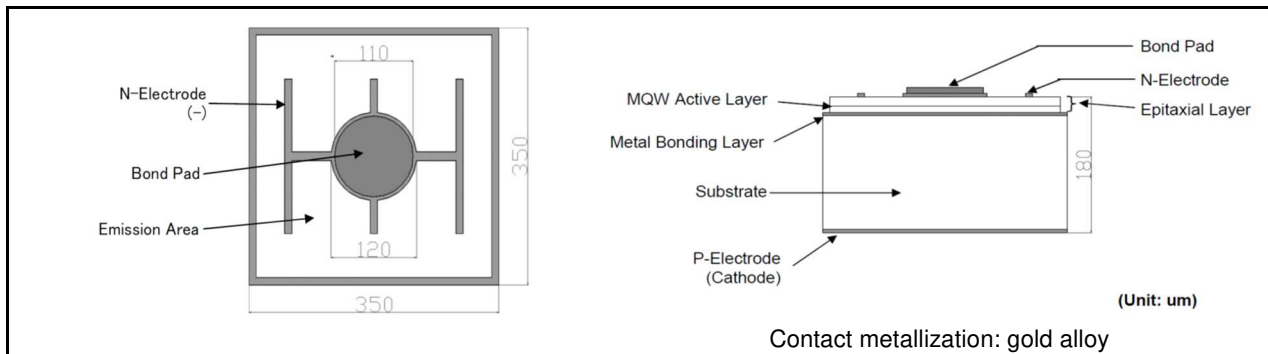
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Infrared LED Chip

EOLC-950-27

Rev. 03, 2020

| Radiation | Type | Electrodes |
|-----------|------------------------------------|----------------|
| Infrared | InAlGaAs epitaxial layer, MQW / Si | n (cathode) up |



Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Test cond. | Symbol | Min | Typ | Max | Unit |
|-----------------|-----------------------|-----------------------|-----|------|-----|---------------|
| Forward voltage | $I_F = 20 \text{ mA}$ | V_F | | 1.25 | | V |
| Reverse current | $V_R = 5 \text{ V}$ | I_R | | | 10 | μA |
| Radiant power* | $I_F = 20 \text{ mA}$ | Φ_e | | 7 | | mW |
| Peak wavelength | $I_F = 20 \text{ mA}$ | λ_p | | 950 | | nm |
| FWHM | $I_F = 20 \text{ mA}$ | $\Delta\lambda_{0.5}$ | | 27 | | nm |
| Rise time | $I_F = 20 \text{ mA}$ | t_r | | 11 | | ns |
| Fall time | $I_F = 20 \text{ mA}$ | t_f | | 10 | | ns |

*Measured on bare chip on TO-18 header

Packing

Dice on adhesive film with wire bond side up.

Art. No. 131 164



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.